FAIRCHILD

SEMICONDUCTOR®

June 2008

FDH5500

N-Channel UltraFET Power MOSFET
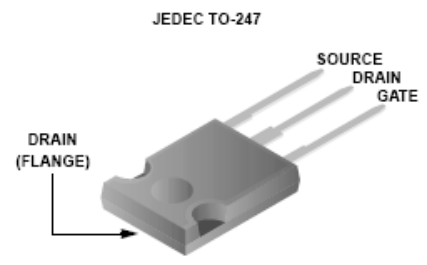
55V, 75A, 7mΩ

Features

- Typ $r_{DS(on)}$ = 5.2mΩ at V_{GS} = 10V, I_D = 75A

- Typ $Q_{g(10)}$ = 118nC at V_{GS} = 10V

- Simulation Models
  - Temperature Compensated PSPICE and SABER™ Models

- Peak Current vs Pulse Width Curve

- UIS Rating Curve

- Related Literature
  - TB334, "Guidelines for Soldering Surface Mount Componets to PC Boards"

- Qualified to AEC Q101
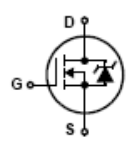
- RoHS Compliant

Applications

- DC Linear Mode Control

- Solenoid and Motor Control

- Switching Regulators

- Automotive Systems

100% RoHS COMPLIANT

Package

JEDEC TO-247

SOURCE
DRAIN
GATE

DRAIN
(FLANGE)

Symbol

D
G
S

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MOSFET Maximum Ratings $T_C = 25°C$ unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain to Source Voltage	(Note 1)	55	V
V_{DGR}	Drain to Gate Voltage ($R_{GS} = 20k\Omega$)	(Note 1)	55	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	Drain Current Continuous ($T_C < 135°C$, $V_{GS} = 10V$)		75	A
	Pulsed		See Figure 4	
E_{AS}	Single Pulse Avalanche Energy	(Note 2)	864	mJ
P_D	Power Dissipation		375	W
	Dreate above 25°C		2.5	W/°C
T_J, T_{STG}	Operating and Storage Temperature		-55 to + 175	°C
T_L	Max. Lead Temp. for Soldering (at 1.6mm from case for 10sec)		300	
T_{pkg}	Max. Package Temp. for Soldering (Package Body for 10sec)		260	

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case	0.4	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-247, 1in^2 copper pad area	30	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDH5500	FDH5500	TO-247	Tube	N/A	30 units

Electrical Characteristics $T_C = 25°C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units

Off Characteristics

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu A$, $V_{GS} = 0V$		55	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 50V$, $V_{GS} = 0V$		-	-	1	μA
		$V_{DS} = 45V$	$T_C = 150°C$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = ±20V$		-	-	±100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu A$	2	2.9	4	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 75A$, $V_{GS} = 10V$	-	5.2	7	mΩ

Dynamic Characteristics

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
C_{iss}	Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, f = 1MHz		-	3565	-	pF
C_{oss}	Output Capacitance			-	1310	-	pF
C_{rss}	Reverse Transfer Capacitance			-	395	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 20V	$V_{GS} = 0$ to 20V	$V_{DD} = 30V$ $I_D = 75A$ $R_L = 0.4\Omega$ $I_g = 1.0mA$	-	206	268	nC
$Q_{g(10)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V		-	118	153	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to 2V		-	6.2	8.1	nC
Q_{gs}	Gate to Source Gate Charge			-	17.8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	51	-	nC

Electrical Characteristics $T_C = 25^oC$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Switching Characteristics						
t_{on}	Turn-On Time	$V_{DD} = 30V$, $I_D = 75A$, $R_L = 0.4\Omega$, $V_{GS} = 10V$, $R_{GS} = 2.5\Omega$	-	-	185	ns
$t_{d(on)}$	Turn-On Delay Time		-	13.7	-	ns
t_r	Rise Time		-	102	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	34	-	ns
t_f	Fall Time		-	22	-	ns
t_{off}	Turn-Off Time		-	-	91	ns
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 75A$	-	1	1.25	V
t_{rr}	Reverse Recovery Time	$I_F = 75A$, $dI_{SD}/dt = 100A/\mu s$	-	60	78	ns
Q_{rr}	Reverse Recovery Charge		-	77	100	nC

Notes:
1: Starting $T_J = 25^oC$ to175^oC.
2: Starting $T_J = 25^oC$, L = 0.48mH, $I_{AS} = 60A$

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/
All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.
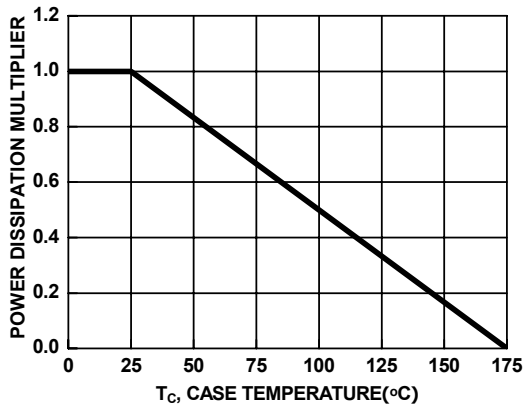
Typical Characteristics

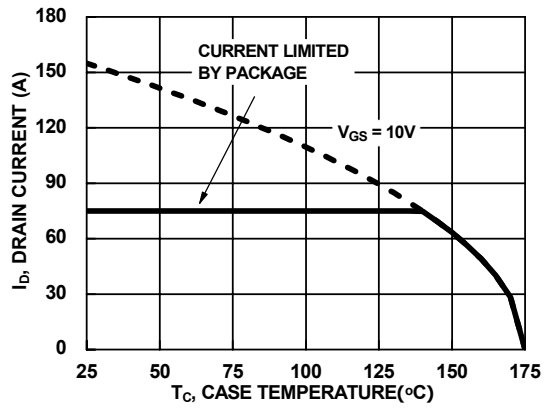**Figure 1. Normalized Power Dissipation vs Case Temperature**

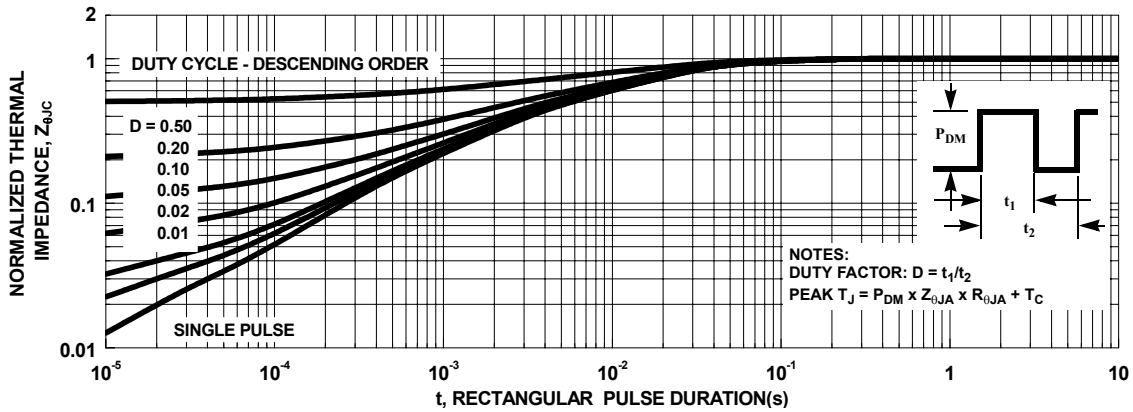**Figure 2. Maximum Continuous Drain Current vs Case Temperature**

NOTES:
DUTY FACTOR: $D = t_1/t_2$
PEAK $T_J = P_{DM} \times Z_{\theta JA} \times R_{\theta JA} + T_C$

Figure 3. Normalized Maximum Transient Thermal Impedance

$T_C = 25^oC$
FOR TEMPERATURES
ABOVE 25°C DERATE PEAK
CURRENT AS FOLLOWS:

$$I = I_2 \left[\sqrt{\frac{175 - T_C}{150}} \right]$$
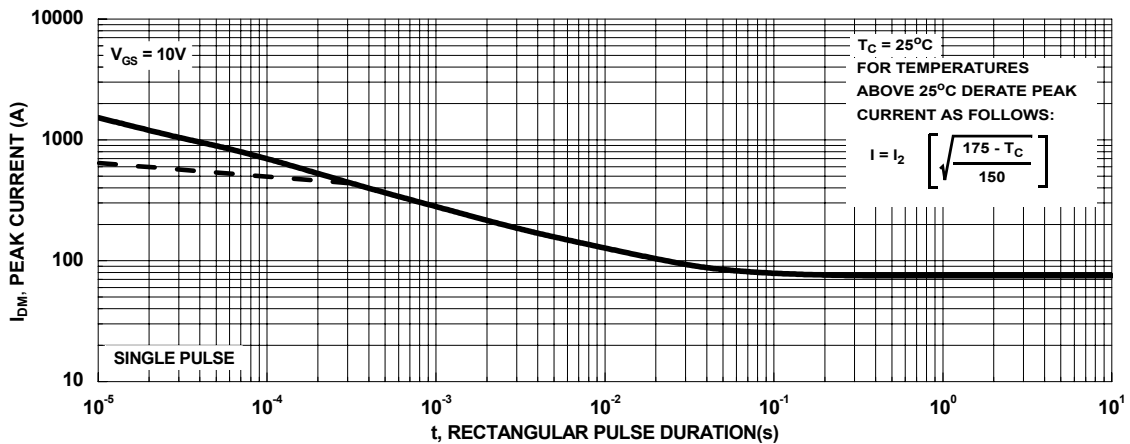
Figure 4. Peak Current Capability

Typical Characteristics
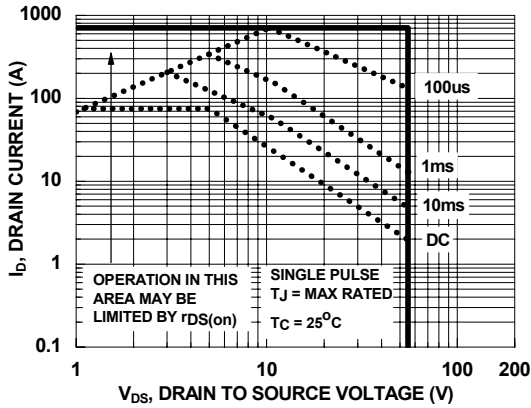
Figure 5. Forward Bias Safe Operating Area
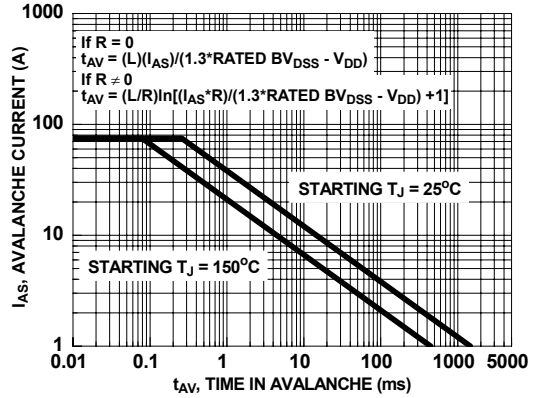
NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability
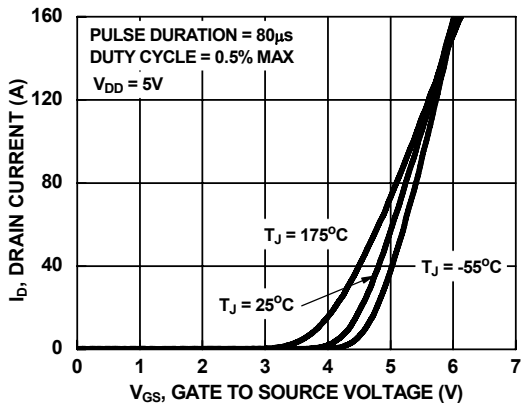
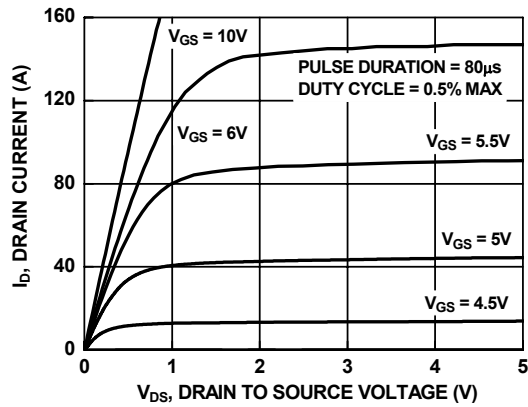Figure 7. Transfer Characteristics

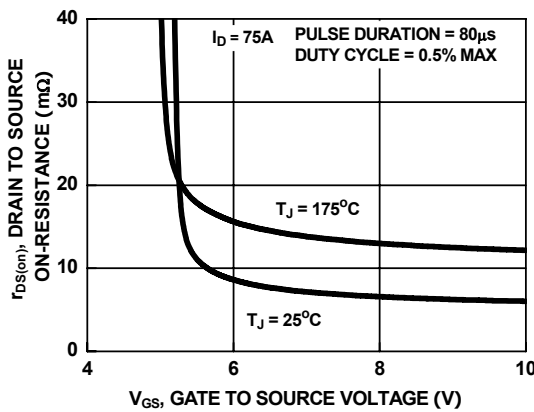
Figure 8. Saturation Characteristics

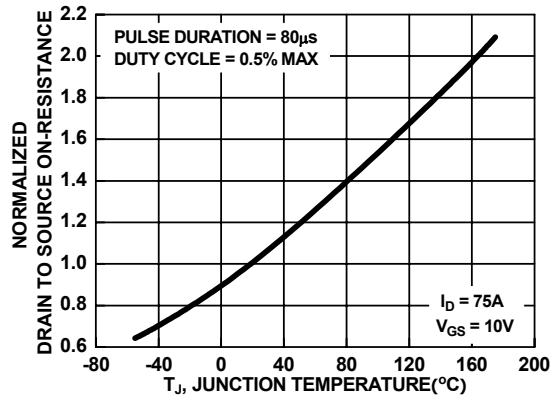Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

FDH5500 N-Channel UltraFET Power MOSFET
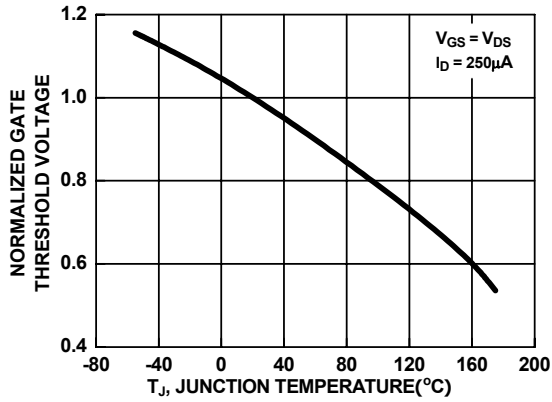
Typical Characteristics

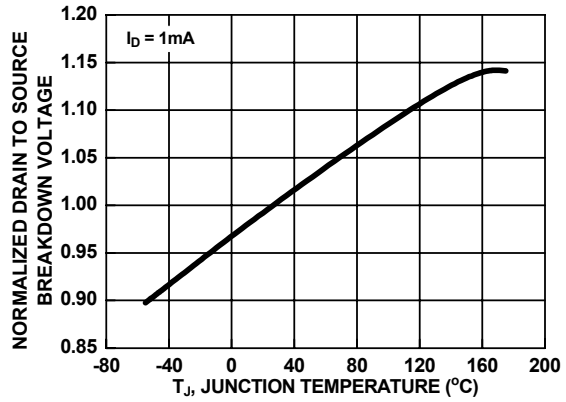Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

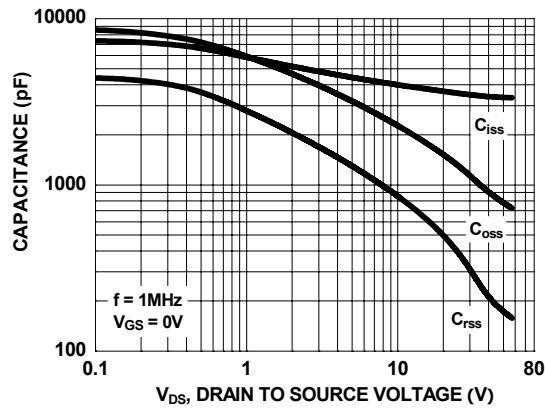Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

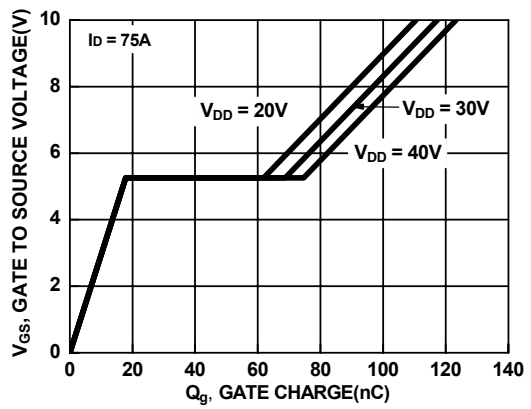Figure 13. Capacitance vs Drain to Source Voltage

Figure 14. Gate Charge vs Gate to Source Voltage

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